

## **RJK0353DPA-01#J0B**

#### RJK0353DPA-01#J0B Information



For Reference Only

Part Number RJK0353DPA-01#J0B

ManufacturerRenesas Electronics AmericaCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 30V 35A 2WPACK

Package 8-PowerWDFN

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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## **RJK0353DPA-01#J0B Specifications**

Manufacturer Part Number  Manufacturer  Renesas Electronics America  Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  8-PowerWDFN  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **Emissions America  Renesas Electronics America  Renesas Electronics America  1
Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  8-PowerWDFN  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  8-PowerWDFN  N-Channel  30V  4.5V, 10V  2.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs  14nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds
Transistors - FETs, MOSFETs - Single  Package 8-PowerWDFN  Series - FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 30V  Current - Continuous Drain (Id) @ 25°C 35A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id 2.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
Package 8-PowerWDFN  Series -  FET Type N-Channel  Technology MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss) 30V  Current - Continuous Drain (Id) @ 25°C 35A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id 2.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
Series - N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 35A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
FET Type  Technology  MOSFET (Metal Oxide)  30V  Current - Continuous Drain (Id) @ 25°C  35A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  N-Channel  N-Channel  N-Channel  N-Channel  N-Channel  130V  25V (Metal Oxide)  35A (Ta)  25V (10V  2.5V (20) 1mA  14nC (20) 4.5V  2180pF (20) 10V
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  35A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  MOSFET (Metal Oxide)  30V  4.5V, 10V  2.5V @ 1mA  2.5V @ 1mA  14nC @ 4.5V  2180pF @ 10V
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  35A (Ta)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  35A (Ta)  4.5V, 10V  2.5V @ 1mA  2.5V @ 1mA  2.5V @ 1mA  2.5V @ 1mA
Current - Continuous Drain (Id) @ 25°C 35A (Ta)  Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V  Vgs(th) (Max) @ Id 2.5V @ 1mA  Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V  Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
Drive Voltage (Max Rds On, Min Rds On)  4.5V, 10V  Vgs(th) (Max) @ Id  Cate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  4.5V, 10V  2.5V @ 1mA  14nC @ 4.5V  2180pF @ 10V
Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  2.5V @ 1mA  14nC @ 4.5V  2180pF @ 10V
Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
Input Capacitance (Ciss) (Max) @ Vds 2180pF @ 10V
$Vgs (Max)$ $\pm 20V$
FET Feature -
Power Dissipation (Max) 40W (Tc)
Rds On (Max) @ Id, Vgs 5.2 mOhm @ 17.5A, 10V
Operating Temperature 150°C (TJ)
Mounting Type Surface Mount
Supplier Device Package 8-WPAK
Package / Case 8-PowerWDFN
Report err

#### RJK0353DPA-01#J0B Guarantees



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### RJK0353DPA-01#J0B Payment Methods



















### RJK0353DPA-01#J0B Shipping Methods













If you have any question about RJK0353DPA-01#J0B, please do not hesitate to contact us!

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